$I_{FAV} = 2x 20 A$



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600 V

35 ns

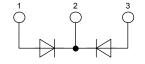
Backside: cathode

Sonic Fast Recovery Diode

High Performance Fast Recove Low Loss and Soft Recovery Common Cathode

Part number

DHG 40 C 600 HB



Package:

 $V_{RRM} =$

- Housing: TO-247
- Industry standard outline
- Epoxy meets UL 94V-0
- RoHS compliant

Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Ratings

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Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RRM}	max. repetitive reverse voltage		$T_{VJ} = 25^{\circ}C$			600	V
I _R	reverse current	V _R = 600 V	$T_{VJ} = 25^{\circ}C$			30	μA
		$V_R = 600 V$	$T_{VJ} = 125^{\circ}C$			3	mΑ
V_{F}	forward voltage	I _F = 20A	$T_{VJ} = 25^{\circ}C$			2.31	V
		$I_F = 40 A$				3.80	V
		I _F = 20 A	T _{VJ} = 150°C			2.15	V
		$I_F = 40 A$				3.00	V
I _{FAV}	average forward current	rectangular, d = 0.5	$T_{c} = 85^{\circ}C$			20	Α
V_{F0}	threshold voltage		$T_{VJ} = 150$ °C			1.31	V
r _F	slope resistance for power loss				36.9	mΩ	
R _{thJC}	thermal resistance junction to case					0.90	K/W
T _{VJ}	virtual junction temperature			-55		150	°C
P_{tot}	total power dissipation		$T_{c} = 25^{\circ}C$			140	W
I _{FSM}	max. forward surge current	t = 10 ms (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			150	Α
I _{RM}	max. reverse recovery current		$T_{VJ} = 25^{\circ}C$		8		Α
		$I_F = 20 \text{ A}; V_R = 400 \text{ V}$	$T_{VJ} = ^{\circ}C$		tbd		Α
t _{rr}	reverse recovery time	$-di_F/dt = 400 A/\mu s$	$T_{VJ} = 25^{\circ}C$		35		ns
			$T_{VJ} = ^{\circ}C$		tbd		ns
CJ	junction capacitance	$V_R = 300 V; f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		tbd		pF

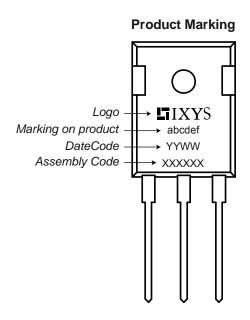


DHG 40 C 600 HB

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			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I _{RMS}	RMS current	per pin ¹⁾			70	Α
R _{thCH}	thermal resistance case to heatsin	k		0.25		K/W
T _{stg}	storage temperature		-55		150	°C
Weight				6		g
M _D	mounting torque		0.8		1.2	Nm
F _c	mounting force with clip		20		120	N

¹⁾ I_{RMS} is typically limited by: 1. pin-to-chip resistance; or by 2. current capability of the chip. In case of 1, a common cathode/anode configuration and a non-isolated backside, the whole current capability can be used by connecting the backside.



Part number

D = Diode

H = Sonic Fast Recovery Diode

G = extreme fast

40 = Current Rating [A]

C = Common Cathode 600 = Reverse Voltage [V]

HB = TO-247AD (3)

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Code Key
Standard	DHG 40 C 600 HB	DHG40C600HB	Tube	30	505145

Similar Part	Package	kage Voltage class	
DHG40C1200HB	TO-247	1200	
DHG40C1200PB	TO-220	1200	
DHG40C600PB	TO-220	600	



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